

subjecting the ion traces of the first and second plurality to a chemical etching process for forming recesses extending from the surface to within the carrier material at an aspect ratio of A from about  $\geq 3$  to about 4 and whereby two or more of such recesses intersect below the surface to form common chambers.

Please amend claim 22 is follows:

22. (Currently amended) The method of claim 21, further including the steps step of blocking at least part of the at least one beam ~~and of selectively decelerating the ions.~~

39. (Currently amended) A system for processing a surface of a dielectric carrier material to adapt it for securely attaching thereto a cover layer by precipitation, comprising:

means for placing the dielectric carrier material in a predetermined position;

means for generating at least one beam of high energy heavy ions along a predetermined path;

means for directing the ions into the carrier material through one surface thereof to form intersecting latent ion traces therein any at least two of which being ~~adapted~~ adapted to be etched into a common volume;

means mounted between the source and the dielectric carrier material for selectively blocking at least a portion of the beam; and

means mounted between the source and the means for blocking for selectively decelerating the ions.

#### Remarks.

The changes to the specification are reflected, with amendatory markings, in one version of a substitute specification and, without such markings, in another version of a substitute specification. This form of amendment, because of the newly introduced section headings, is thought to be more convenient to the Examiner than would be amended paragraphs shown